

## O I P INFORMATION DISCLOSURE CITATION

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NOV 03 2003

ATTY DOCKET NO.  
ITO.0552US (P16160)SERIAL NO.  
10/634,140APPLICANT(S):  
TYLER A. LOWREYFILING DATE:  
August 4, 2003GROUP ART UNIT:  
2826

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.						
B.						
C.						
D.						

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
E.						
F.						
G.						
H.						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

I.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 <sup>th</sup> IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003
J.	Ha, Y.H., Yi, J.H., Horii, H., Park, J.H., Joo, S.H., Park, S.O., Chung, U-In and Moon, J.T., "An Edge Contact Type Cell for Phase Change RAM Featuring Very Low Power Consumption," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
K.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Oh, J.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Chung, U.I., Jeong, H.S. and Kim, Kinam, "Full Integration and Reliability Evaluation of Phase-change RAM Based on 0.24 mm-CMOS Technologies," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
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M.	
N.	
O.	

EXAMINER

DATE CONSIDERED

03/02/05

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					ATTY DOCKET NO. ITO.0552US (P16160)	SERIAL NO. 10/634,140	
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)					APPLICANT(S): Tyler A. Lowrey		
FILING DATE: August 4, 2004					GROUP ART UNIT: 2826		
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>J. L.</i>	A.	6,579,760	06/17/2003	Lung	438	257	—
	B.						
	C.						
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U.S. PATENT APPLICATION PUBLICATIONS							
<i>J. L.</i>	F.	2003/0001230	01/02/2003	Lowrey	257	529	—
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	J.						
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<i>J. L.</i>	K.	DD 251 225	11/04/1987	German			X
<i>J. L.</i>	L.	WO 99/44258	09/02/1999	PCT			
<i>J. L.</i>	M.	WO 2004/055828	07/01/2004	PCT			
<i>J. L.</i>	N.	WO 2004/055899	07/01/2004	PCT			
	O.						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	Q.						
	R.						
	S.						
	T.						
	U.						
	V.						
EXAMINER	<i>J. L. Lowrey</i>			DATE CONSIDERED	<i>03/02/05</i>		
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